

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











WIDEBAND LNA MODULE, 1 - 12 GHz

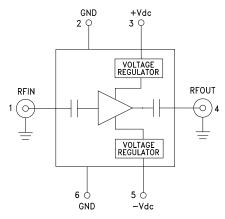


Typical Applications

The HMC-C059 Wideband LNA is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation
- Industrial Sensors

Functional Diagram



Features

Noise Figure: 1.8 dB @ 8 GHz High Gain: 16 dB @ 8 GHz

P1dB Output Power: +16 dBm @ 8 GHz

Spurious-Free Operation

Regulated Supply and Bias Sequencing

Hermetically Sealed Module

Field Replaceable SMA connectors

-55 °C to +85 °C Operating Temperature

General Description

The HMC-C059 is a GaAs MMIC pHEMT Low Noise Distributed Amplifier in a miniature, hermetic module with replaceable SMA connectors which operates between 1 and 12 GHz. The amplifier provides 16 dB of gain, 1.8 dB noise figure, and up to +17 dBm of output power at 1 dB gain compression. The wideband amplifier I/Os are internally matched to 50 Ohms and are internally DC blocked. Integrated voltage regulators allow for flexible biasing of both the negative and positive supply pins, while internal bias sequencing circuitry assures robust operation.

Electrical Specifications, $T_A = +25^{\circ} \text{ C}$, +Vdc = +6V, -Vdc = -5V

Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range	1 - 8		8 - 12		GHz		
Gain	14	16		12	14		dB
Gain Flatness		±1			±1.25		dB
Gain Variation Over Temperature		0.005			0.005		dB/ °C
Noise Figure		1.75	2.25		2.5	3	dB
Input Return Loss		-12			-7		dB
Output Return Loss		-17			-15		dB
Output Power for 1 dB Compression (P1dB)		17			14		dBm
Saturated Output Power (Psat)		19			17		dBm
Output Third Order Intercept (IP3)		31			29		dBm
Positive Supply Current (+IDC)		60	70		60	70	mA
Negative Supply Current (-IDC)		1.5			1.5		mA

HMC-C059* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS 🖵

View a parametric search of comparable parts.

DOCUMENTATION

Application Notes

 AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers

Data Sheet

· HMC-C059 Data Sheet

DESIGN RESOURCES 🖵

- HMC-C059 Material Declaration
- · PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

DISCUSSIONS

View all HMC-C059 EngineerZone Discussions.

SAMPLE AND BUY 🖳

Visit the product page to see pricing options.

TECHNICAL SUPPORT 🖳

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK 🖳

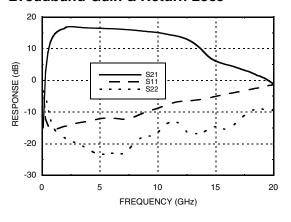
Submit feedback for this data sheet.



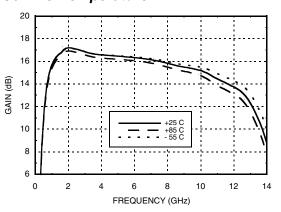
WIDEBAND LNA MODULE, 1 - 12 GHz



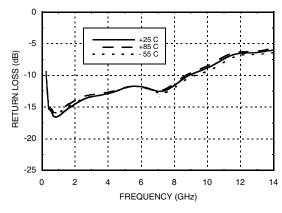
Broadband Gain & Return Loss



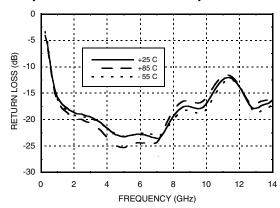
Gain vs. Temperature



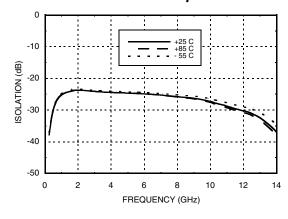
Input Return Loss vs. Temperature



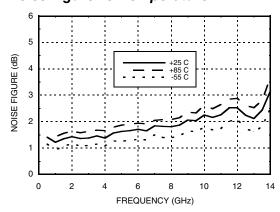
Output Return Loss vs. Temperature



Reverse Isolation vs. Temperature



Noise Figure vs. Temperature

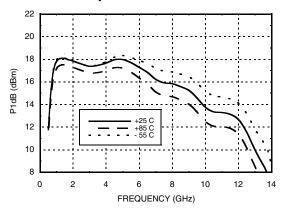




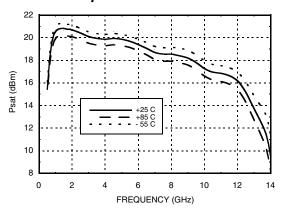


WIDEBAND LNA MODULE, 1 - 12 GHz

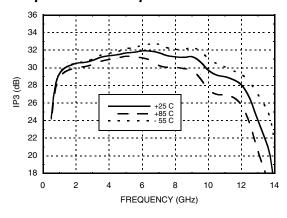
P1dB vs. Temperature



Psat vs. Temperature



Output IP3 vs. Temperature



Absolute Maximum Ratings

Positive Bias Supply Voltage (+Vdc)	+16V	
Negative Bias Supply (-Vdc)	-12V	
RF Input Power (RFIN)	+10 dBm	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-55 to +85 °C	



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS





WIDEBAND LNA MODULE, 1 - 12 GHz

Pin Descriptions

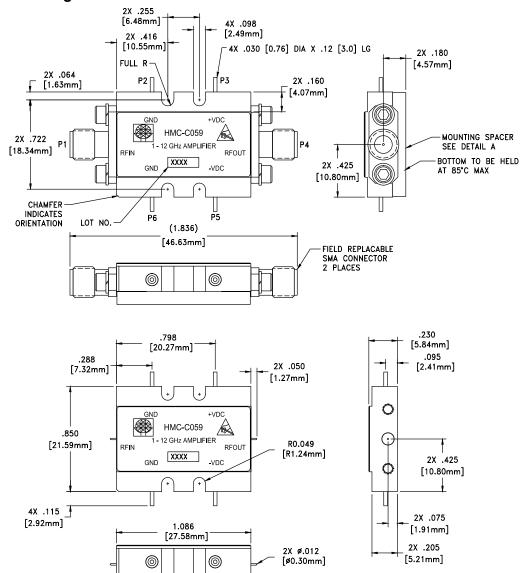
Pin Number	Function	Description	Interface Schematic	
1	RFIN & RF Ground	RF input connector, SMA female, field replaceable. This pin is AC coupled and matched to 50 Ohms.	RFIN 0—	
2, 6	GND	Power supply ground.	GND	
3	+Vdc	Positive power supply voltage for the amplifier.	+Vdc O VOLTAGE REGULATOR	
4	RFOUT & RF Ground	RF output connector, SMA female. This pin is AC coupled and matched to 50 Ohms.		
5	-Vdc	Negative power supply voltage for the amplifier	-Vdc ○ VOLTAGE REGULATOR	





WIDEBAND LNA MODULE, 1 - 12 GHz

Outline Drawing



VIEW SHOWN WITH CONNECTORS AND MOUNTING SPACER REMOVED

Package Information

Package Type	C-10			
Package Weight [1]	18.7 gms ^[2]			
Spacer Weight	3.3 gms ^[2]			

[1] Includes the connectors

[2] ±1 gms Tolerance

NOTES:

- 1. PACKAGE, LEADS, COVER MATERIAL: KOVAR™
- 2. FINISH: GOLD PLATE OVER NICKEL PLATE
- 3. ALL DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 4. TOLERANCES:
 - 4.1 .XX = ±0.02
 - $4.2.XXX = \pm 0.010$
- 5. FIELD REPLACEABLE 2.92mm CONNECTORS TENSOLITE 231CCSF OR EQUIVALENT



WIDEBAND LNA MODULE, 1 - 12 GHz



ANALOGDEVICES

Notes: